





# HIGH EFFICIENCY CLASS-G ADSL LINE DRIVER

#### **FEATURES**

- Low Total Power Consumption Increases ADSL Line Card Density (20 dBm on Line)
  - 600 mW w/Active Termination (Full Bias)
  - 530 mW w/Active Termination (Low Bias)
- Low MTPR of -74 dBc (All Bias Conditions)
- High Output Current of 500 mA (typ)
- Wide Supply Voltage Range of ±5 V to ±15 V [V<sub>CC(H)</sub>] and ±3.3 V to ±15 V [V<sub>CC(L)</sub>]
- Wide Output Voltage Swing of 43 Vpp Into 100-Ω Differential Load [V<sub>CC(H)</sub> = ±12 V]
- Multiple Bias Modes Allow Low Quiescent Power Consumption for Short Line Lengths
  - 160-mW/ch Full Bias Mode
  - 135-mW/ch Mid Bias Mode
  - 110-mW/ch Low Bias Mode
  - 75-mW/ch Terminate Only Mode
  - 13-mW/ch Shutdown Mode
- Low Noise for Increased Receiver Sensitivity
  - 3.3 pA/√Hz Noninverting Current Noise
  - 9.5 pA/√Hz Inverting Current Noise
  - 3.5 nV/√Hz Voltage Noise

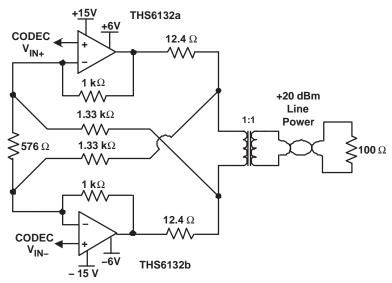
#### **APPLICATIONS**

 Ideal for Active Termination Full Rate ADSL DMT applications (20-dBm Line Power)

#### DESCRIPTION

The THS6132 is a Class-G current feedback differential line driver ideal for full rate ADSL DMT systems. Its extremely low power consumption of 600 mW or lower is ideal for ADSL systems that must achieve high densities in ADSL central office rack applications. The unique patent pending architecture of the THS6132 allows the quiescent current to be much lower than existing line drivers while still achieving very high linearity. In addition, the multiple bias settings of the amplifiers allow for even lower power consumption for line lengths where the full performance of the amplifier is not required. The output voltage swing has been vastly improved over first generation Glass-G amplifiers and allows the use of lower power supply voltages that help conserve power. For maximum flexibility, the THS6132 can be configured in classical Class-AB mode requiring only as few as one power supply.

### Typical ADSL CO Line Driver Circuit Utilizing Active Impedance Supporting A 6.3 Crest Factor



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage.

#### ORDERING INFORMATION

PRODUCT	PACKAGE	PACKAGE CODE	SYMBOL	TA	ORDER NUMBER	TRANSPORT MEDIA
TUCC420\/ED	TOED SO Davis DADIM	VED 00	TI 100422		THS6132VFP	Tube
THS6132VFP	TQFP-32 PowerPAD™	VFP-32	THS6132	-40°C to 85°C	THS6132VFPR	Tape and reel
THS6132RGW	Leadless 25-pin 5,mm x 5, mm PowerPAD™	RGW-25	6132	-40 0 10 03 0	THS6132RGWR	Tape and reel

#### PACKAGE DISSIPATION RATINGS

PACKAGE	ΘЈА	ΘJC	$T_A \le 25^{\circ}C$ POWER RATING(1)	T <sub>A</sub> = 70°C POWER RATING(1)	T <sub>A</sub> = 85°C POWER RATING <sup>(1)</sup>
VFP-32	29.4°C/W	0.96°C/W	3.57 W	2.04 W	1.53 W
RGW-25	31°C/W	1.7°C/W	3.39 W	1.94 W	1.45 W

<sup>(1)</sup> Power rating is determined with a junction temperature of 130°C. This is the point where distortion starts to substantially increase. Thermal management of the final PCB should strive to keep the junction temperature at or below 125°C for best performance.

#### **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted(1)

		THS6132
Supply voltage	e, V <sub>CC(H)</sub> and V <sub>CC(L)</sub> (2)	±16.5 V
Input voltage, \	V <sub>I</sub>	±VCC(L)
Output current	, I <sub>O</sub> (3)	900 mA
Differential inp	ut voltage, V <sub>IO</sub>	±2 V
Maximum junc	tion temperature, T <sub>J</sub> (see Dissipation Rating Table for more information)	150°C
Operating free	-air temperature, T <sub>A</sub>	-40°C to 85°C
Storage tempe	rature, T <sub>Stg</sub>	65°C to 150°C
Lead temperat	ure, 1,6 mm (1/16-inch) from case for 10 seconds	300°C
	НВМ	1 kV
ESD ratings	CDM	500 V
	MM	200 V

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

<sup>(2)</sup>  $V_{CC(H)}$  must always be greater than or equal to  $V_{CC(L)}$  for proper operation. Class-AB mode operation occurs when  $V_{CC(H)}$  is equal to  $V_{CC(L)}$  and is considered acceptable operation for the THS6132 even though it is not fully specified in this mode of operation.

<sup>(3)</sup> The THS6132 incorporates a PowerPAD on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipating plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature that could permanently damage the device. See TI Technical Brief SLMA002 for more information about utilizing the PowerPAD thermally enhanced package.



# **RECOMMENDED OPERATING CONDITIONS**

		MIN	NOM	MAX	UNIT
Committee	+VCC(H) to -VCC(H)	$\pm V_{CC(L)}$	±15	±16	.,
Supply voltage	+VCC(L) to $-VCC(L)$	±3.3	±5	±V <sub>CC(H)</sub>	V
Operating free-air t	emperature, T <sub>A</sub>	-40		85	°C

# **ELECTRICAL CHARACTERISTICS**

over recommended operating free-air temperature range,  $T_A = 25^{\circ}C$ ,  $V_{CC(H)} = \pm 15$  V,  $V_{CC(L)} = \pm 5$  V  $R_F = 1.5$  k $\Omega$ , Gain = +10, Full Bias Mode,  $R_L = 50$   $\Omega$  (unless otherwise noted)

NOISE	E/DISTORTION PER			T CONDITIONS		T)/D		
	PARAMETE  Multitone power ratio		Gain =+11, 163kHz +20 dBm Line Powe	r, 1:1.1 transformer,	MIN	<b>TYP</b> -74	MAX	dBc
	Receive band spill-over			ynthesis factor = 4 o 138 kHz with MTPR signal		<b>–95</b>		dBc
	· ·		applied	Differential load = 100 Ω		-84		
	Harmonic distortion	(Differential	2 <sup>nd</sup> harmonic	Differential load = $100 \Omega$		-69		dBc
HD		Configuration, f = 1 MHz,		Differential load = $20.02$				
	$V_{O(PP)} = 2 \text{ V}, \text{ Gain} = +10)$		3 <sup>rd</sup> harmonic	Differential load = $25 \Omega$		-73		dBc
Vn	Input voltage noise		f = 10 kHz			3.5		nV/√Hz
_		+Input	6 40111		3.3		A / /	
In	Input current noise —Input		f = 10 kHz		9.5			pA/√Hz
	Crosstalk		f = 1  MHz, $R_L = 100 \Omega,$	$V_O(PP) = 2 V$ , Gain = +2		-52		dBc
OUTP	UT CHARACTERIS	TICS	•					
			V	R <sub>L</sub> = 100 Ω	±10.4	±10.8		V
Vo	Single-ended outpu	t voltago ewing	V <sub>CC(H)</sub> = ±12 V	$R_L = 30 \Omega$	±9.9	±10.4		V
VO	Single-ended odipa	t voltage swing	V <sub>CC(H)</sub> = ±15 V	$R_L = 100 \Omega$	±13.3	±13.8		V
			VCC(H) - ±13 V	$R_L = 50 \Omega$	±13	±13.6		v
	Output voltage trans	ition from V <sub>CC(L)</sub> to	$R_1 = 50 \Omega$	$V_{CC(L)} = \pm 5 \text{ V}$		±3.1		V
	V <sub>CC(H)</sub> (Point wher	e ICC(L) = ICC(H)	TT_ 00 22	VCC(L) = ±6 V		±3.9		, i
lo	Output current (1)		$R_{I} = 10 \Omega$	$V_{CC(H)} = \pm 12 \text{ V}$		±500		mA
.0		(1)		$V_{CC(H)} = \pm 15 \text{ V}$	±400	±500		
I(SC)	Short-circuit current	(1)	$R_L = 1 \Omega$	$V_{CC(H)} = \pm 15 \text{ V}$		±750		mA
	Output resistance		Open-loop			5		Ω
	Output resistance—		f = 1 MHz,	Gain = +10		0.35		Ω
	Output resistance—	shutdown mode	f = 1 MHz,	Open-loop		5.5		kΩ

<sup>(1)</sup> A heatsink is required to keep the junction temperature below absolute maximum rating when an output is heavily loaded or shorted. See Absolute Maximum Ratings section for more information.



# **ELECTRICAL CHARACTERISTICS (continued)**

over recommended operating free-air temperature range,  $T_A = 25^{\circ}C$ ,  $V_{CC(H)} = \pm 15$  V,  $V_{CC(L)} = \pm 5$  V RF = 1.5 k $\Omega$ , Gain = +10, Full Bias Mode,  $R_L = 50 \Omega$  (unless otherwise noted)

POWER	R SUPPLY								
	PARAMETER	TES"	CONDITIONS	MIN	TYP	MAX	UNIT		
Vasus	Operating rooms	±V <sub>CC(H)</sub>		±VCC(L)	±15	±16.5	٧		
VCC(x)	Operating range	±V <sub>CC(L)</sub>		±3	±5	±VCC(H)	V		
		$V_{CC(L)} = \pm 5 \text{ V};$	T <sub>A</sub> = 25°C	5.7	6.4	7.5	mA		
		(V <sub>CC(H)</sub> =±15 V)	T <sub>A</sub> = full range			8.1	ША		
	Quiescent current (each driver) Full-bias mode	$V_{CC(L)} = \pm 6 \text{ V};$	T <sub>A</sub> = 25°C		6.7		A		
	(Bias-1 = 1, Bias-2 = 1,	$(V_{CC(H)} = \pm 15 \text{ V})$	T <sub>A</sub> = full range				mA		
	Bias-3 = X) (Icc trimmed with $V_{CC(H)} = \pm 15 \text{ V}$ , $V_{CC(L)} = \pm 5 \text{ V}$ )	(Icc trimmed with $V_{CC(H)} = \pm 15 \text{ V}$ ,	Bias-3 = X)	$V_{CC(H)} = \pm 12 \text{ V};$	T <sub>A</sub> = 25°C		3.1		mA
			$(V_{CC(L)} = \pm 5 \text{ V})$	T <sub>A</sub> = full range				ША	
		$V_{CC(H)} = \pm 15 \text{ V};$	$T_A = 25^{\circ}C$	2.9	3.25	3.75	mA		
1		$(V_{CC(L)} = \pm 5 \text{ V})$	T <sub>A</sub> = full range			4.25			
Icc		Mid; Bias $-1 = 1$ , Bias $-2 = 0$ , Bias $-3 = 1$		5.0	5.6	6.8	mA		
	Quiescent current (each driver) Variable bias modes,	Low; Bias-1 = 1, Bias-2 = 0, Bias-3 = 0		4.25	4.8	6.0			
	$V_{CC(L)} = \pm 5 \text{ V}$	Terminate; Bias-1 = 0, Bias-2 = 1, Bias-3 = X(1)		3.2	3.8	4.5			
		Shutdown; Bias-1 =		1	1.3				
		Mid; Bias-1 = 1, Bias	-2 = 0, Bias-3 = 1	2.4	2.7	3.0			
	Quiescent current (each driver) Variable bias modes,	Low ; Bias-1 = 1, Bia	s-2 = 0, Bias-3 = 0	1.9	2.15	2.4	A		
	$V_{CC(H)} = \pm 15 \text{ V}$	Terminate; Bias-1 = 0	), Bias-2 = 1, Bias-3 = X(1)	1.1	1.3	1.5	mA		
	00(11)	Shutdown ; Bias-1 =	0, Bias-2 = 0, Bias-3 = $X(1)$		0.1	0.5			
		Vacan IEV	T <sub>A</sub> = 25°C	-70	-82				
DODD	Power supply rejection ratio	$V_{CC(L)} = \pm 5V$	T <sub>A</sub> = full range	-68			dB		
PSRR	$(\Delta V_{CC(x)} = \pm 1 \text{ V})$	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	T <sub>A</sub> = 25°C	-70	-82		uБ		
	• •	$V_{CC(H)} = \pm 15V$	T <sub>A</sub> = full range	-68					

<sup>(1)</sup> X is used to denote a logic state of either 1 or 0.



ELECTRICAL CHARACTERISTICS (continued) over recommended operating free-air temperature range,  $T_A = 25^{\circ}C$ ,  $V_{CC(H)} = \pm 15$  V,  $V_{CC(L)} = \pm 5$  V RF = 1.5 kΩ, Gain = +10, Full Bias Mode,  $R_L = 50$  Ω (unless otherwise noted)

DYNAMIC PERFORMANCE								
	PARAMETER	ARAMETER TEST CONDITIONS		MIN	TYP	MAX	UNIT	
			Gain = +1, RF = 750 $\Omega$		80			
		D. 100 O	Gain = +2, RF = 620 $\Omega$		70		MHz	
	Single-ended small-signal bandwidth	$R_L = 100 \Omega$	Gain = +5, RF = $500 \Omega$		60			
DIM			Gain = +10, RF = 1 k $\Omega$	20				
BW	$(-3 \text{ dB}), V_0 = 0.1 \text{ Vrms}$		Gain = +1, RF = 750 $\Omega$		60			
		D 05.0	Gain = +2, RF = 620 $\Omega$		55	MHz		
		$R_L = 25 \Omega$	Gain = +5, RF = $500 \Omega$		50			
			Gain = +10, RF = 1 k $\Omega$		17			
SR	Single-ended slew-rate(1)	V <sub>O</sub> = 20 V <sub>PP</sub> ,	Gain =+10		300		V/μs	

<sup>(1)</sup> Slew-rate is defined from the 25% to the 75% output levels

DC PE	RFORMANCE						
	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
	lanut effect voltage		T <sub>A</sub> = 25°C		1	15	
	Input offset voltage		T <sub>A</sub> = full range			20	mV
Vos	Differential effect voltage	$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T <sub>A</sub> = 25°C		0.3	6	
	Differential offset voltage		T <sub>A</sub> = full range			8	
	Offset drift		T <sub>A</sub> = full range		40		μV/°C
	land thing assument		T <sub>A</sub> = 25°C		1	15	
	-Input bias current	V 15.V 16.V	T <sub>A</sub> = full range			20	
I <sub>IB</sub>		$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T <sub>A</sub> = 25°C		1.5	15	μΑ
	+ Input bias current		T <sub>A</sub> = full range			20	
Z <sub>OL</sub>	Open loop transimpedance	$R_L = 1 \text{ k}\Omega$	•		2		МΩ



# **ELECTRICAL CHARACTERISTICS (continued)**

over recommended operating free-air temperature range, T<sub>A</sub> = 25°C,  $V_{CC(H)}$  = ±15 V,  $V_{CC(L)}$  = ±5 V R<sub>F</sub> = 1.5 k $\Omega$ , Gain = +10, Full Bias Mode, R<sub>L</sub> = 50  $\Omega$  (unless otherwise noted)

INPUT	INPUT CHARACTERISTICS								
	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT		
		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	T <sub>A</sub> = 25°C	±2.7	±3.0				
V <sub>ICR</sub> Ir	Input common-mode voltage range(1)	$V_{CC(L)} = \pm 5 \text{ V}$	T <sub>A</sub> = full range	±2.6			V		
		$V_{CC(L)} = \pm 6 \text{ V}$	$T_A = 25^{\circ}C$		±4.0				
	REF pin input voltage range	V <sub>CC</sub> -(L)= ±5 V			±2.5		V		
	REF pili iliput voltage range	V <sub>CC(L)</sub> = ±6 ∨			±3.5		V		
CMDD	Common-mode rejection ratio	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	$T_A = 25^{\circ}C$	60	67		dB		
CMRR	Common-mode rejection ratio	$V_{CC(L)} = \pm 5 \text{ V}, \pm 6 \text{ V}$	T <sub>A</sub> = full range	57			uБ		
В	Input resistance	+ Input			800		kΩ		
R <sub>I</sub>	input resistance	- Input			45	·	Ω		
C <sub>I</sub>	Differential Input capacitance				1.2	·	pF		

<sup>(1)</sup> To conserve as much power as possible, the input stage of the THS6132 is powered from the  $V_{CC(L)}$  supplies and is limited by the  $V_{CC(L)}$  supply voltage. For Class-AB operation, connect the  $V_{CC(L)}$  supplies to  $V_{CC(H)}$ .

LOGIC CONTROL CHARACTERISTICS								
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
VIH	Bias pin voltage for logic 1	Relative to DGND pin voltage	2.0			V		
VIL	Bias pin voltage for logic 0	Relative to DGND pin voltage			0.8	V		
lн	Bias pin current for logic 1	V <sub>IH</sub> = 5 V, DGND = 0 V		-0.1	-0.2	μΑ		
IIL	Bias pin current for logic 0	V <sub>IL</sub> = 0 V, DGND = 0 V		-0.1	-0.2	μΑ		
	Transition time—logic 0 to logic 1 <sup>(1)</sup>			0.1		μs		
	Transition time—logic 1 to logic 0 <sup>(1)</sup>			0.2		μs		
	DGND useable range		-VCC(H)		+VCC(H) -5	V		

<sup>(1)</sup> Transition time is defined as the time from when the logic signal is applied to the time when the supply current has reached half its final value.

LOGIC	LOGIC TABLE								
BIAS-1	BIAS-2	BIAS-3	DESCRIPTION						
1	1	χ(1)	Full bias mode	Amplifiers ON with lowest distortion possible					
1	0	1	Mid bias mode	Amplifiers ON with power savings with a reduction in distortion performance					
1	0	0	Low bias mode	Amplifiers ON with enhanced power savings and a reduction of distortion performance					
0	1	χ(1)	Terminate mode	Lowest power state with +Vin pins internally connect to REF pin and output has low impedance					
0	0	χ(1)	Shutdown mode	Amplifiers OFF and output has high impedance					

<sup>(1)</sup> X is used to denote a logic state of either 1 or 0.

NOTE: The default state for all logic pins is a logic one (1).



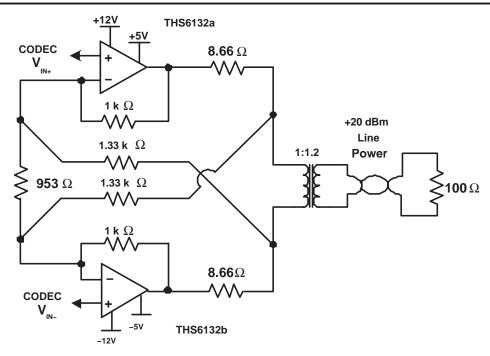
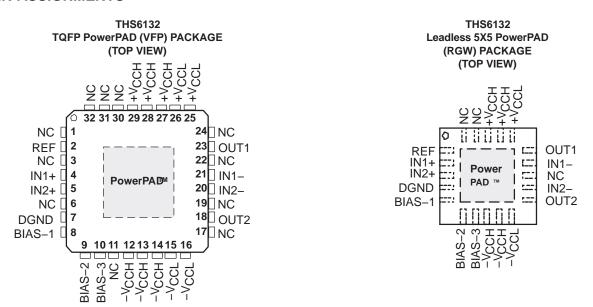


Figure 1. ±12 V Active Termination ADSL CO Line Driver Circuit (Synthesis Factor = 4; CF = 5.6)

#### **PIN ASSIGNMENTS**



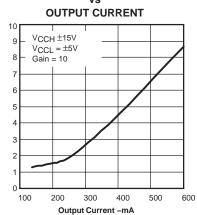


# TYPICAL CHARACTERISTICS

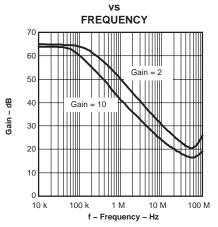
# **Table of Graphs**

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# OUTPUT VOLTAGE HEADROOM vs



# **COMMON-MODE REJECTION RATIO**



CROSSTALK vs

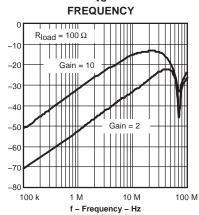


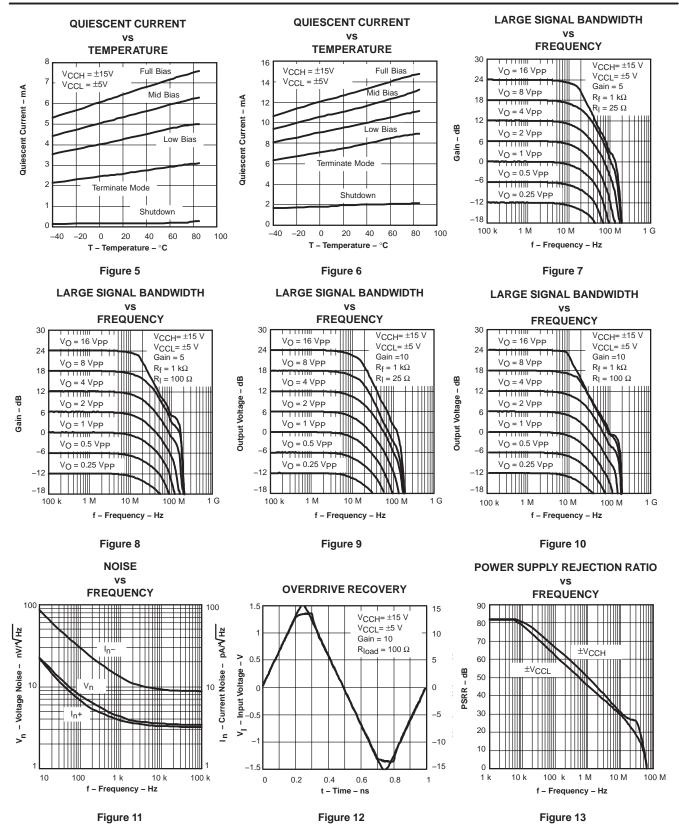
Figure 2

Figure 3

Figure 4

Output Voltage Headroom - VCC - Vout







#### **SMALL SIGNAL FREQUENCY RESPONSE**

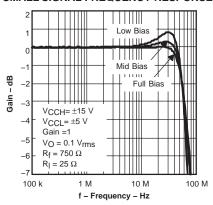


Figure 14

SMALL SIGNAL FREQUENCY RESPONSE SMALL SIGNAL FREQUENCY RESPONSE

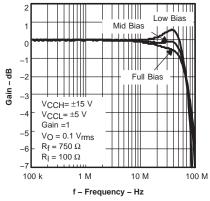


Figure 15

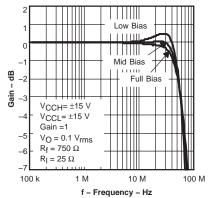


Figure 16
SMALL SIGNAL BANDWIDTH

**SMALL SIGNAL BANDWIDTH** 

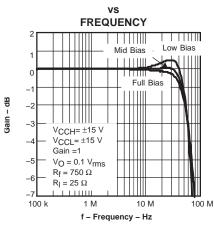


Figure 17

SMALL SIGNAL BANDWIDTH

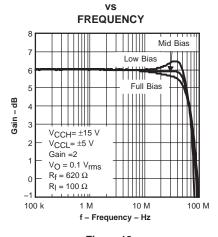


Figure 18

VS
FREQUENCY

8
7
Low Bias

7
Low Bias

7
VCCH=±15 V
VCCL=±15 V
VCCL=±15 V
Gain =2
VO = 0.1 Vrms
0 R<sub>f</sub> = 620 Ω
R<sub>l</sub> = 25 Ω
100 k 1 M 10 M 100 M
f - Frequency - Hz

Figure 19

#### **SMALL SIGNAL BANDWIDTH**

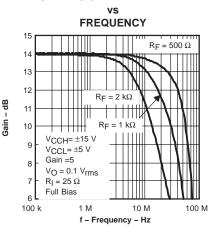


Figure 20

#### SMALL SIGNAL BANDWIDTH

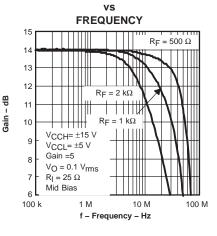


Figure 21

#### **SMALL SIGNAL BANDWIDTH**

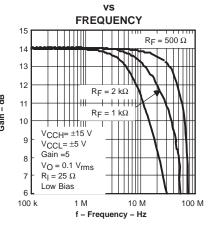
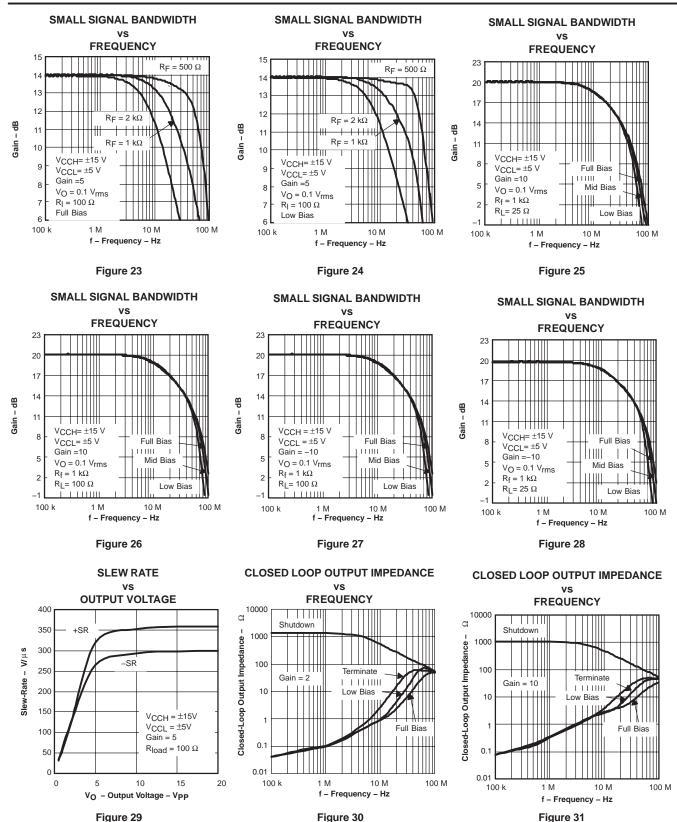
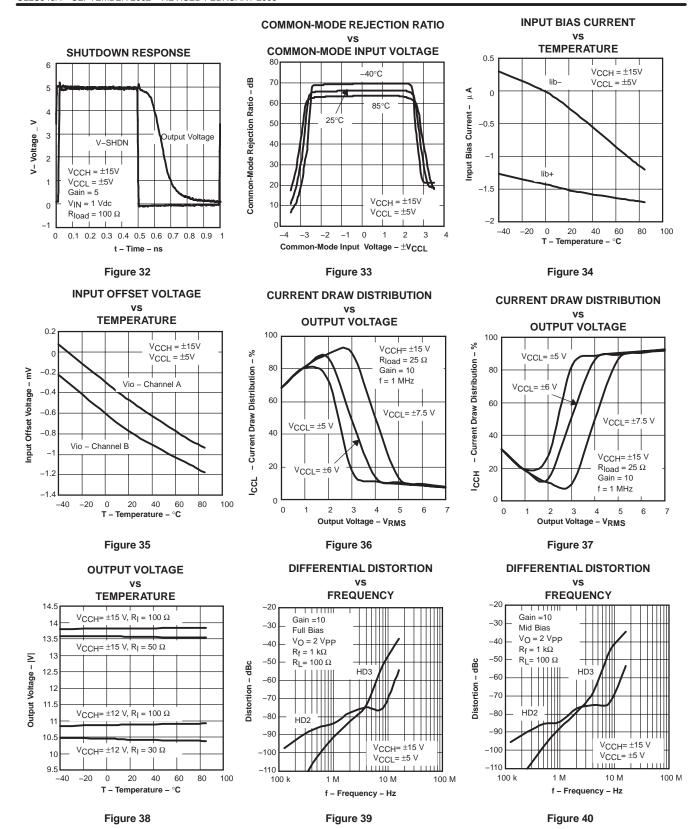


Figure 22

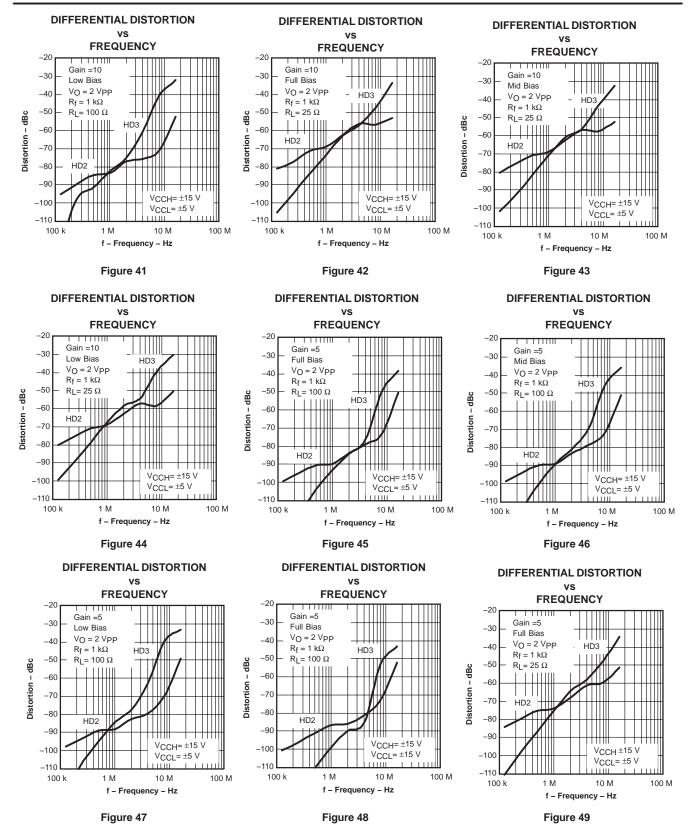




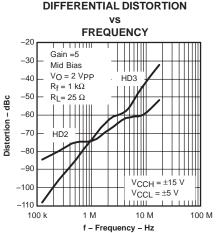












**FREQUENCY** -20 Gain =5 -30 Low Bias V<sub>O</sub> = 2 V<sub>PP</sub> HD3 -40  $R_f = 1 k\Omega$ -50 R<sub>L</sub>= 25 Ω -60 -70 HD2 -80 -90 V<sub>CCH</sub> = ±15 V -100 V<sub>CCL</sub> = ±5 V -110 100 k 10 M 100 M f - Frequency - Hz

**DIFFERENTIAL DISTORTION** 

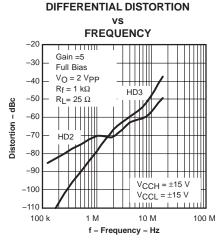
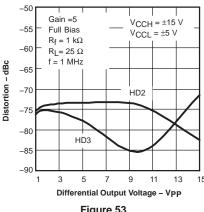


Figure 50

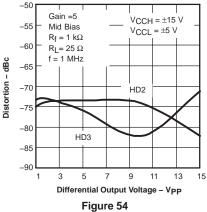
Figure 51

Figure 52

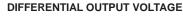
#### **DIFFERENTIAL DISTORTION** vs **DIFFERENTIAL OUTPUT VOLTAGE**



**DIFFERENTIAL DISTORTION** vs **DIFFERENTIAL OUTPUT VOLTAGE** 



**DIFFERENTIAL DISTORTION** vs



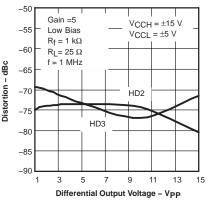


Figure 53

**DIFFERENTIAL DISTORTION** 

**DIFFERENTIAL OUTPUT VOLTAGE** 

**DIFFERENTIAL DISTORTION** 

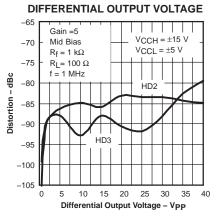
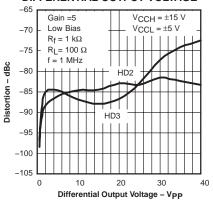


Figure 55

#### **DIFFERENTIAL DISTORTION** VS **DIFFERENTIAL OUTPUT VOLTAGE**



VCCH = ±15 V Full Bias -70 VCCL = ±5 V  $R_f = 1 k\Omega$ -75 R<sub>L</sub>= 100 Ω f = 1 MHz Distortion – dBc -80 HD<sub>2</sub> -85 -90 HD3 -95

Figure 56

15 20

Differential Output Voltage - Vpp

25

Figure 57

Figure 58

-65

-100

-105

Gain =5



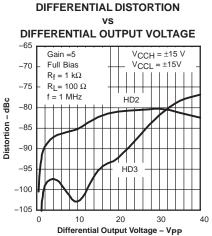


Figure 59

#### **DIFFERENTIAL OUTPUT VOLTAGE** -50 Gain =10 V<sub>CCL</sub> = ±15 V V<sub>CCL</sub> = ±5V Full Bias -55 $R_f = 1 k\Omega$ -60 R<sub>L</sub>= 25 Ω f = 1 MHz HD2 -65 Distortion -70 -75 -80 HD3 -85 -90 11 13 15 Differential Output Voltage - Vpp

**DIFFERENTIAL DISTORTION** 

Figure 60

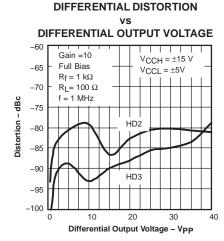


Figure 61

#### **DIFFERENTIAL DISTORTION** vs **DIFFERENTIAL OUTPUT VOLTAGE**

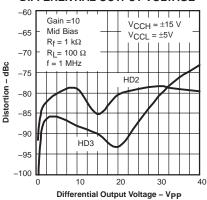


Figure 62

#### **DIFFERENTIAL DISTORTION** VS **DIFFERENTIAL OUTPUT VOLTAGE** -60 Gain =10 V<sub>CCH</sub> = ±15 V -65 Low Bias

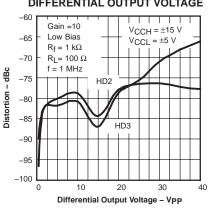


Figure 63

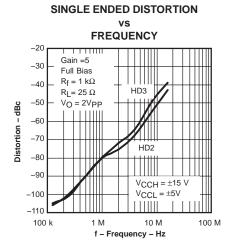


Figure 64

#### SINGLE ENDED DISTORTION

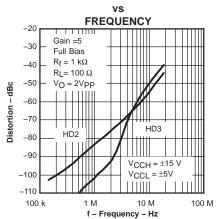


Figure 65





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#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
THS6132RGWR	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS6132RGWRG4	ACTIVE	QFN	RGW	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS6132VFP	ACTIVE	HLQFP	VFP	32	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS6132VFPG4	ACTIVE	HLQFP	VFP	32		TBD	Call TI	Call TI
THS6132VFPR	ACTIVE	HLQFP	VFP	32	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS6132VFPRG4	ACTIVE	HLQFP	VFP	32	1000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

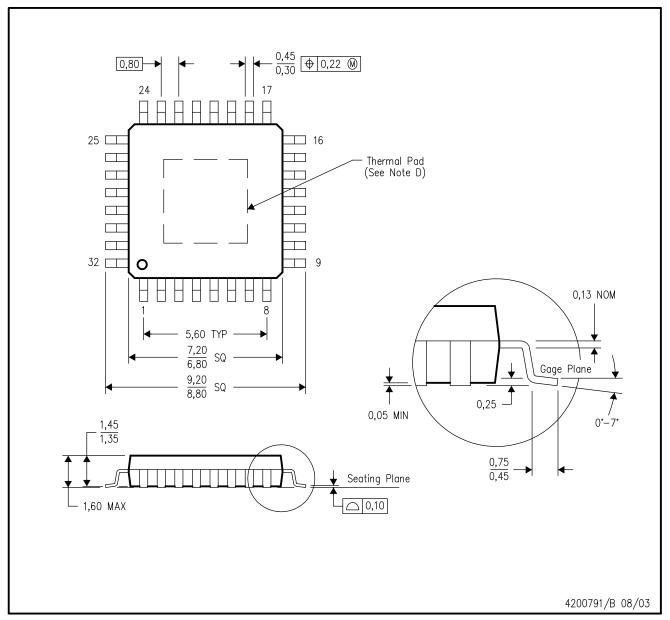
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# VFP (S-PQFP-G32)

# PowerPAD™ PLASTIC QUAD FLATPACK

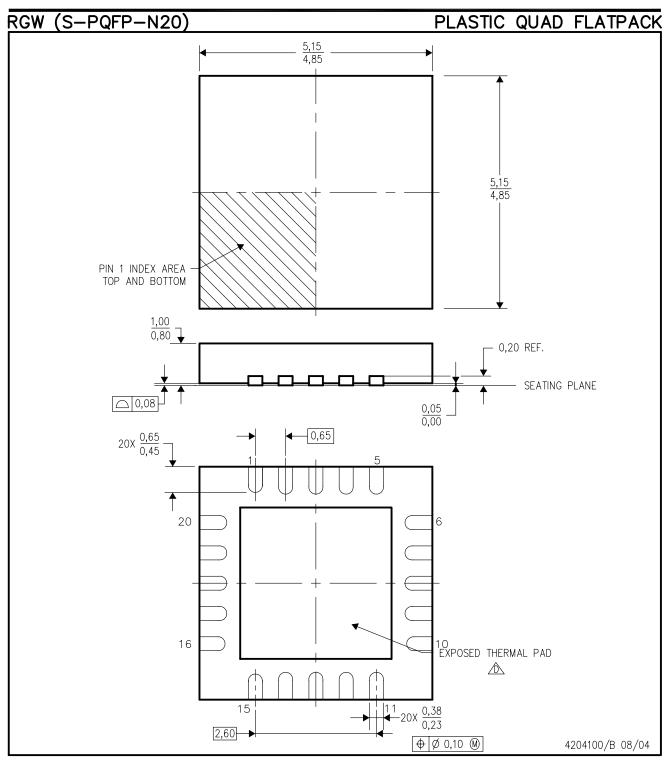


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="https://www.ti.com">www.ti.com</a>.
- E. Falls within JEDEC MS-026
- F. PowerPad is a trademark of Texas Instruments Incorporated.

PowerPAD is a trademark of Texas Instruments.





NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5—1994.

- B. This drawing is subject to change without notice.
- C. Quad Flat pack, No-leads (QFN) package configuration
- The package thermal pad must be soldered to the board for thermal and mechanical performance..
  - See the Product Data Sheet for details regarding the exposed thermal pad dimensions.
- E. Falls within JEDEC MO-220.



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